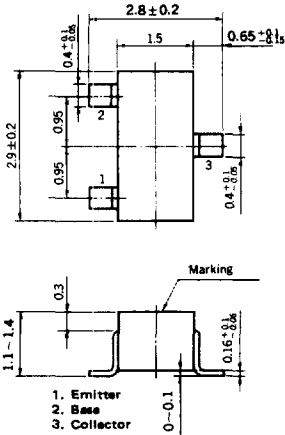


SILICON TRANSISTOR

2SD596

AUDIO FREQUENCY POWER AMPLIFIER NPN SILICON EPITAXIAL TRANSISTOR MINI MOLD

PACKAGE DIMENSIONS in millimeters



DESCRIPTION

The 2SD596 is designed for use in small type equipments especially recommended for hybrid integrated circuit and other applications.

FEATURES

- Micro package.
- High DC current gain. $h_{FE} : 200$ TYP. ($V_{CE} = 1.0$ V, $I_C = 100$ mA)
- Complimentary to NEC 2SB624 PNP Transistor.

ABSOLUTE MAXIMUM RATINGS

Maximum Voltages and Current ($T_a = 25^\circ\text{C}$)

Collector to Base Voltage	V_{CBO}	30	V
Collector to Emitter Voltage	V_{CEO}	25	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current (DC)	I_C	700	mA

Maximum Power Dissipation

Total Power Dissipation at 25°C Ambient Temperature	P_T	200	mW
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Maximum Temperatures

Storage Temperature Range	T_{stg}	-55 to +150	$^\circ\text{C}$
Operating Junction Temperature	T_j	150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Collector Cutoff Current	I_{CBO}			100	nA	$V_{CB} = 30$ V, $I_E = 0$
Emitter Cutoff Current	I_{EBO}			100	nA	$V_{EB} = 5.0$ V, $I_C = 0$
DC Current Gain	h_{FE1}	110	200	400		$V_{CE} = 1.0$ V, $I_C = 100$ mA *
DC Current Gain	h_{FE2}	50				$V_{CE} = 1.0$ V, $I_C = 700$ mA *
Base to Emitter Voltage	V_{BE}	600	640	700	mV	$V_{CE} = 6.0$ V, $I_C = 10$ mA *
Collector Saturation Voltage	$V_{CE(sat)}$		0.22	0.6	V	$I_C = 700$ mA, $I_B = 70$ mA *
Output Capacitance	C_{ob}		12		pF	$V_{CB} = 6.0$ V, $I_E = 0$, $f = 10$ MHz
Gain Bandwidth Product	f_T		170		MHz	$V_{CE} = 6.0$ V, $I_E = -10$ mA

* Pulsed: $PW \leq 350$ μs , Duty Cycle $\leq 2\%$

h_{FE1} Classification

Marking	DV1	DV2	DV3	DV4	DV5
h_{FE}	110 to 180	135 to 220	170 to 270	200 to 320	250 to 400

TYPICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

